

ABSTRACT OF THE DISCLOSURE

SILICATE GATE DIELECTRIC

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5 A method of forming a silicate dielectric having superior
electrical properties comprising forming a metal oxide
layer on a Si-containing semiconductor material and
reacting the metal oxide with the underlying Si-
10 containing material in the presence of an oxidizing gas
is provided. Semiconductor structures comprising the
metal silicate formed over a SiO_2 layer are also
disclosed herein.

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